

**Vishay Siliconix** 

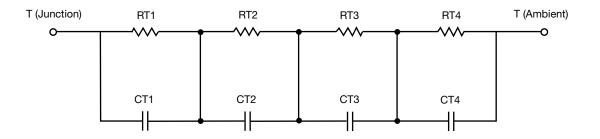
# **R-C Thermal Model Parameters**

#### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



<b>R-C VALUES FOR TANK</b>	CONFIGURATION		
	THERMAL RES	ISTANCE (°C/W)	
Junction to	Ambient	Case	Foot
RT1	n/a	61.5928m	n/a
RT2	n/a	100.1833m	n/a
RT3	n/a	60.3032m	n/a
RT4	n/a	77.9207m	n/a
·	THERMAL CAPAC	ITANCE (Joules/°C)	
Junction to	Ambient	Case	Foot
CT1	n/a	659.0748m	n/a
CT2	n/a	3.8563m	n/a
CT3	n/a	65.8195m	n/a
CT4	n/a	406.9649m	n/a

Note

• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

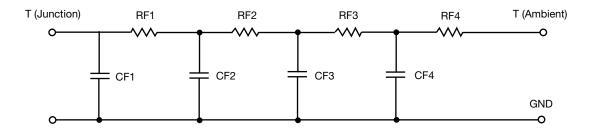
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### **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	n/a	123.4088m	n/a		
RF2	n/a	84.4132m	n/a		
RF3	n/a	18.5195m	n/a		
RF4	n/a	73.6585m	n/a		
	THERMAL CAPAC	CITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	3.9059m	n/a		
CF2	n/a	80.3887m	n/a		
CF3	n/a	39.1860m	n/a		
CF4	n/a	380.4652m	n/a		

Note

• n/a indicates not applicable



SUG80050E\_RC

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